NSN 5961-00-835-7919

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-835-7919 **Inclosure Material:** Metal **Overall Length:** 0.260 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.335 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 75.0 breakdown voltage, collector-to-base, emitter open all transistor and 40.0 breakdown voltage, collector-to-emitter, base open all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** 500.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 300.0 milliwatts small-signal input power, common-collector preset all transistor **Transfer Ratio:** 30.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 6 uninsulated wire lead **Specification Data:** 80131-release3892 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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No